
Poster Presentation

[AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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[AMDp1-24L]High mobility p-type tin oxide thin-film by adopting passivation layer

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Keywords:p-type SnO, thin-film transistors, SiO₂ passivation

The effects of SiO₂ passivation on tin monoxide (SnO) semiconductor was investigated. In X-ray photoelectron spectroscopy studies revealed that the tail-state above valence band maximum was clearly detected in SiO₂- capped SnO film which may improve the p-type conductivity. As a result, the resulting SnO thin-film transistors show enhanced electrical properties.